

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet A1 of 1



## Complete if Known

Application Number	10772,882
Filing Date	February 5, 2004
First Named Inventor	Saxder
Group Art Unit	2811
Examiner Name	Jerome Jackson, Jr.
Attorney Docket Number	5308-389

## U.S. PATENTS AND PATENT PUBLICATIONS

Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (If known)		
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	2. 6,586,781			Wu et al.	07-01-2003
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Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (If known)			
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	17. PCT	WO 01/57929 A1			Cree Lighting Company	08-09-2001	
	18. JP	10-050982			Nippon Telegraph & Telephone Corp.	02-20-1998	
	19. EP	0 563 847 A2			Matsushita Electric Industrial Co., Ltd.	10-06-1993	

## OTHER NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
	20.	Breitschadet et al., "Minimization of Leakage Current of Recessed Gate AlGaN/GaN HEMTs by Optimizing the Dry-Etching Process," <i>Journal of Electronic Materials</i> , Vol. 28, No. 12 (1999).	
	21.	Burm et al., "Recessed Gate GaN MODFETs," <i>Solid State Electronics</i> , Vol. 41, No. 2, pp. 247-50 (1997)	
	22.	Chen et al., "Reactive ion etching for gate recessing of AlGaN/GaN Field-effect transistors," <i>J. Vac. Sci. Technol. B</i> , Vol. 17, No. 6, (1999).	
	23.	Egawa et al., "Recessed gate AlGaN/GaN modulation-doped field-effect transistors on sapphire," <i>Applied Physics Letters</i> , Vol. 76, No. 1, pp. 121-23 (2000).	
	24.	Heitman et al., "Polarization Effects in AlGaN/GaN and GaN/AlGaN/GaN heterostructures," <i>Journal of Applied Physics</i> , Vol. 93, No. 12, pp. 10114-118 (2003).	
	25.	Heitman, Sten J., <i>MOCVD Growth Technologies for Applications in Al/GaN/GaN High Electron Mobility Transistors</i> , Dissertation, University of California—Santa Barbara, 190 pages (2002).	
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	30.	Sriram et al., "RF Performance of AlGaN/GaN MODFETs on High Resistivity SiC Substrates," Presentation at Materials Research Society Fall Symposium, 1997.	
	31.	Sriram et al., "SiC and GaN Wide Bandgap Microwave Power Transistors," <i>IEEE Samoff Symposium</i> , March 18, 1998.	

Examiner Signature		Date Considered	D/J/T
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.